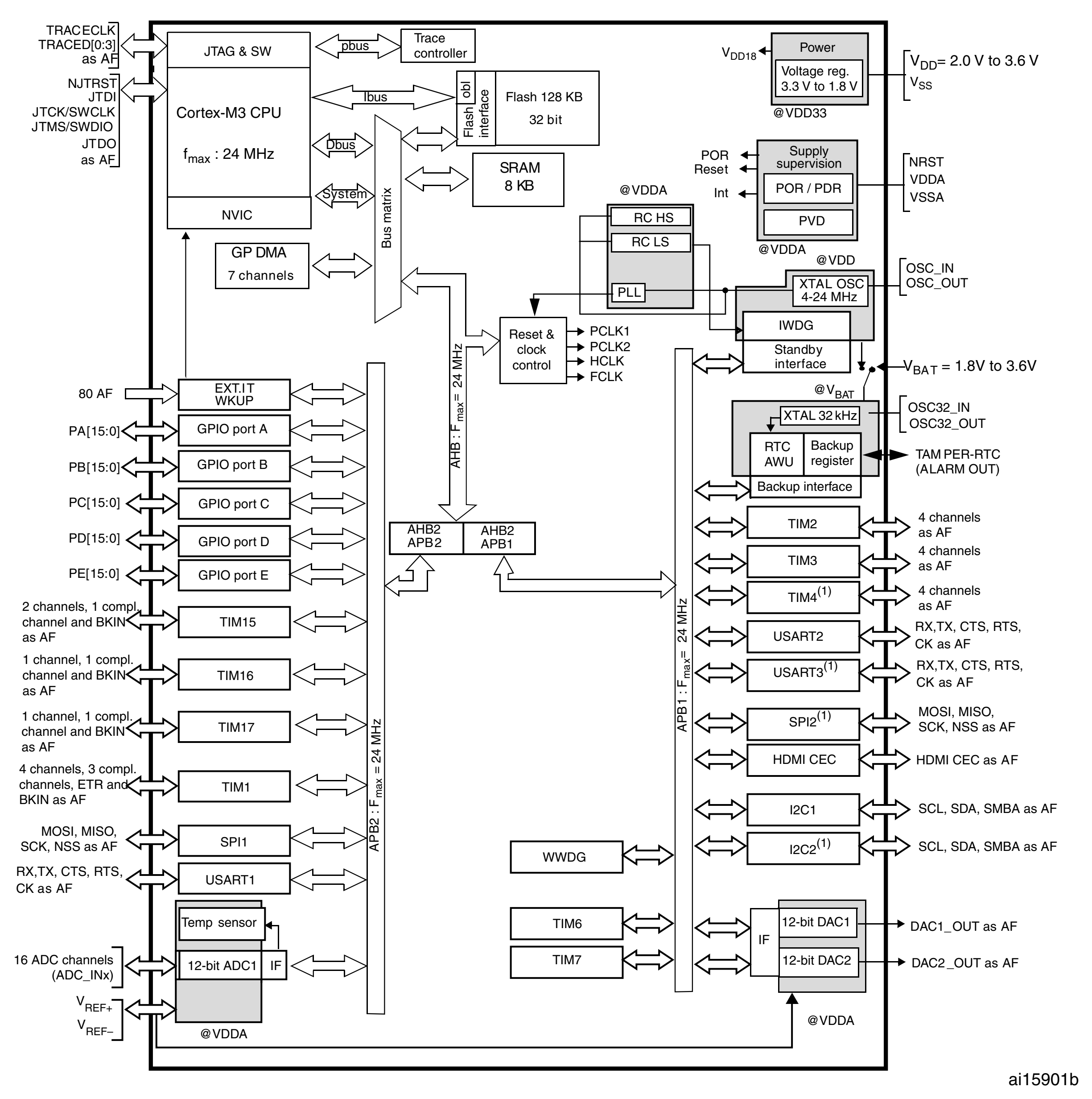
Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100r8t6b

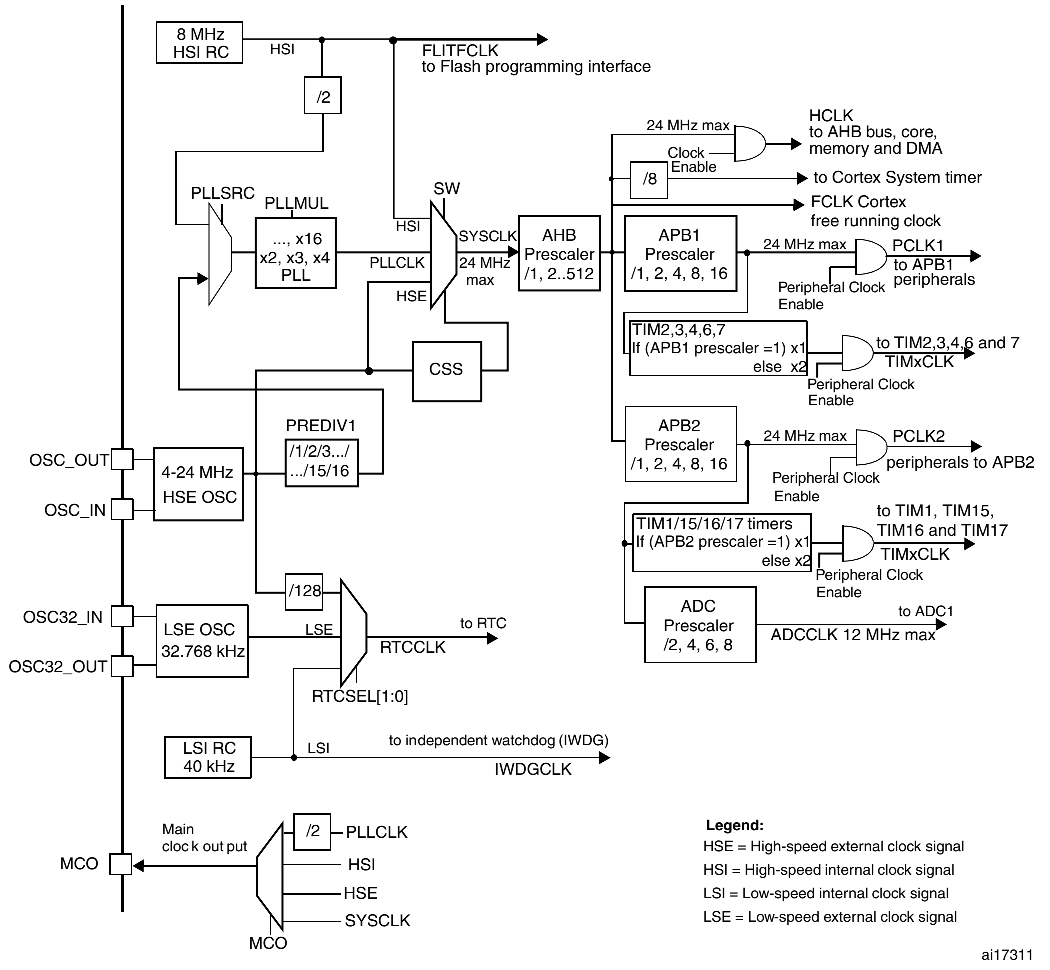
List of tables

Figure 1. STM32F100xx value line block diagram



1. Peripherals not present in low-density value line devices.
2. AF = alternate function on I/O port pin.
3. T_A = –40 °C to +85 °C (junction temperature up to 105 °C) or T_A = –40 °C to +105 °C (junction temperature up to 125 °C).

Figure 2. Clock tree



1. To have an ADC conversion time of 1.2 µs, APB2 must be at 24 MHz.

Table 4. Low & medium-density STM32F100xx pin definitions (continued)

Pins				Pin name	Type(1)	I / O level(2)	Main function(3) (after reset)	Alternate functions(3)(4)	
LQFP100	LQFP64	TFBGA64	LQFP48					Default	Remap
33	24	H5	-	PC4	I/O	-	PC4	ADC1_IN14	-
34	25	H6	-	PC5	I/O	-	PC5	ADC1_IN15	-
35	26	F5	18	PB0	I/O	-	PB0	ADC1_IN8/TIM3_CH3(12)	TIM1_CH2N
36	27	G5	19	PB1	I/O	-	PB1	ADC1_IN9/TIM3_CH4(12)	TIM1_CH3N
37	28	G6	20	PB2	I/O	FT	PB2/BOOT1	-	-
38	-	-	-	PE7	I/O	FT	PE7	-	TIM1_ETR
39	-	-	-	PE8	I/O	FT	PE8	-	TIM1_CH1N
40	-	-	-	PE9	I/O	FT	PE9	-	TIM1_CH1
41	-	-	-	PE10	I/O	FT	PE10	-	TIM1_CH2N
42	-	-	-	PE11	I/O	FT	PE11	-	TIM1_CH2
43	-	-	-	PE12	I/O	FT	PE12	-	TIM1_CH3N
44	-	-	-	PE13	I/O	FT	PE13	-	TIM1_CH3
45	-	-	-	PE14	I/O	FT	PE14	-	TIM1_CH4
46	-	-	-	PE15	I/O	FT	PE15	-	TIM1_BKIN
47	29	G7	21	PB10	I/O	FT	PB10	I2C2_SCL(9)/USART3_TX(12)	TIM2_CH3 / HDMI_CEC
48	30	H7	22	PB11	I/O	FT	PB11	I2C2_SDA(9)/USART3_RX(12)	TIM2_CH4
49	31	D6	23	V_{SS_1}	S	-	V_{SS_1}	-	-
50	32	E6	24	V_{DD_1}	S	-	V_{DD_1}	-	-
51	33	H8	25	PB12	I/O	FT	PB12	SPI2_NSS(10)/ I2C2_SMBA(9)/ TIM1_BKIN(12)/USART3_CK(12)	-
52	34	G8	26	PB13	I/O	FT	PB13	SPI2_SCK(10) /TIM1_CH1N(12) USART3_CTS(12)	-
53	35	F8	27	PB14	I/O	FT	PB14	SPI2_MISO(10)/ TIM1_CH2N(12) / USART3_RTS(12)	TIM15_CH1
54	36	F7	28	PB15	I/O	FT	PB15	SPI2_MOSI(10) / TIM1_CH3N / TIM15_CH1N(12)	TIM15_CH2
55	-	-	-	PD8	I/O	FT	PD8	-	USART3_TX
56	-	-	-	PD9	I/O	FT	PD9	-	USART3_RX

4 Memory mapping

The memory map is shown in *Figure 7*.

Figure 7. Memory map

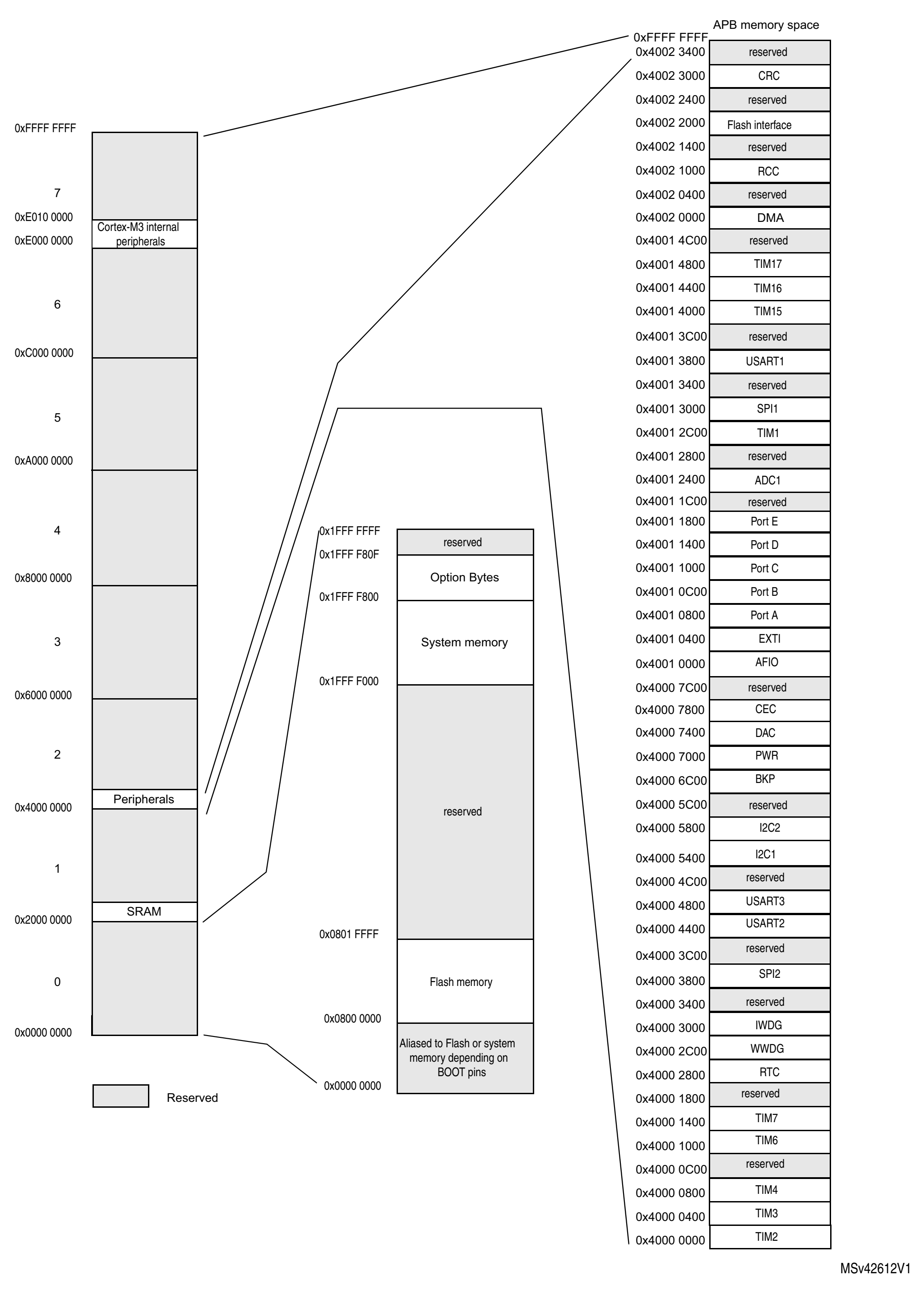
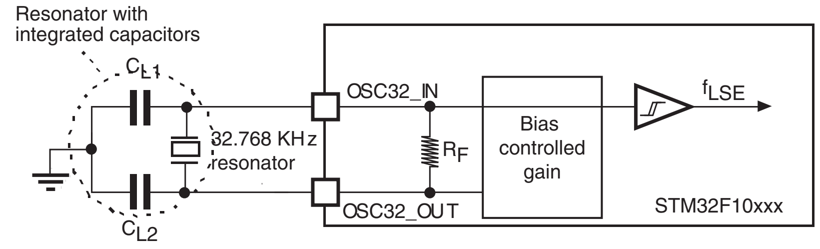


Table 16. Typical current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions	f_{HCLK}	Typical values[(1)]		Unit
				All peripherals enabled[(2)]	All peripherals disabled	
I_{DD}	Supply current in Run mode	Running on high-speed external clock with an 8 MHz crystal[(3)]	24 MHz	12.8	9.3	mA
			16 MHz	9.3	6.6	
			8 MHz	5.1	3.9	
			4 MHz	3.2	2.5	
			2 MHz	2.1	1.75	
			1 MHz	1.55	1.4	
			500 kHz	1.3	1.2	
			125 kHz	1.1	1.05	
		Running on high-speed internal RC (HSI)	24 MHz	12.2	8.6	
			16 MHz	8.5	6	
			8 MHz	4.6	3.3	
			4 MHz	2.6	1.9	
			2 MHz	1.5	1.15	
			1 MHz	0.9	0.8	
			500 kHz	0.65	0.6	
			125 kHz	0.45	0.43	

1. Typical values are measures at T_A = 25 °C, V_{DD} = 3.3 V.
2. Add an additional power consumption of 0.8 mA for the ADC and of 0.5 mA for the DAC analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).
3. An 8 MHz crystal is used as the external clock source. The AHB prescaler is used to reduce the frequency when f_{HCLK} < 8 MHz, the PLL is used when f_{HCLK} > 8 MHz.

Figure 21. Typical application with a 32.768 kHz crystal



ai14129b

5.3.7 Internal clock source characteristics

The parameters given in *Table 23* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 8*.

High-speed internal (HSI) RC oscillator

Table 23. HSI oscillator characteristics[1]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	8	-	MHz
$DuCy_{(HSI)}$	Duty cycle	-	45	-	55	%
ACC_{HSI}	Accuracy of HSI oscillator	T_A = –40 to 105 °C[2]	-2.4	-	2.5	%
		T_A = –10 to 85 °C[2]	-2.2	-	1.3	%
		T_A = 0 to 70 °C[2]	-1.9	-	1.3	%
		T_A = 25 °C	-1	-	1	%
$t_{su(HSI)}$[3]	HSI oscillator startup time	-	1	-	2	µs
$I_{DD(HSI)}$[3]	HSI oscillator power consumption	-	-	80	100	µA

1. V_{DD} = 3.3 V, T_A = –40 to 105 °C °C unless otherwise specified.
2. Guaranteed by characterization results.
3. Guaranteed by design. Not tested in production

Low-speed internal (LSI) RC oscillator

Table 24. LSI oscillator characteristics [1]

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}	Frequency	30	40	60	kHz
$\Delta f_{LSI(T)}$	Temperature-related frequency drift[2]	-9	-	9	%
$t_{su(LSI)}$[3]	LSI oscillator startup time	-	-	85	µs
$I_{DD(LSI)}$[3]	LSI oscillator power consumption	-	0.65	1.2	µA

1. V_{DD} = 3 V, T_A = –40 to 105 °C °C unless otherwise specified.
2. Guaranteed by characterization results.
3. Guaranteed by design.

Wakeup time from low-power mode

The wakeup times given in *Table 25* are measured on a wakeup phase with an 8-MHz HSI RC oscillator. The clock source used to wake up the device depends from the current operating mode:

- Stop or Standby mode: the clock source is the RC oscillator
- Sleep mode: the clock source is the clock that was set before entering Sleep mode.

All timings are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 8*.

Table 25. Low-power mode wakeup timings

Symbol	Parameter	Typ	Unit
$t_{WUSLEEP}$[1]	Wakeup from Sleep mode	1.8	µs
t_{WUSTOP}[1]	Wakeup from Stop mode (regulator in run mode)	3.6	µs
	Wakeup from Stop mode (regulator in low-power mode)	5.4	
$t_{WUSTDBY}$[1]	Wakeup from Standby mode	50	µs

1. The wakeup times are measured from the wakeup event to the point at which the user application code reads the first instruction.

5.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (Electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 29*. They are based on the EMS levels and classes defined in application note AN1709.

Table 29. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 24 MHz, LQFP100 package, conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{HCLK} = 24 MHz, LQFP100 package, conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and pre qualification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second. To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

SPI interface characteristics

Unless otherwise specified, the parameters given in *Table 41* are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 8*.

Refer to *Section 5.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 41. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	12	MHz
		Slave mode	-	12	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF		8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$(1)	NSS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(NSS)}$(1)	NSS hold time	Slave mode	$2t_{PCLK}$	-	
$t_{w(SCKH)}$(1) $t_{w(SCKL)}$(1)	SCK high and low time	Master mode, f_{PCLK} = 24 MHz, presc = 4	50	60	
$t_{su(MI)}$ (1) $t_{su(SI)}$(1)	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}$ (1)	Data input hold time	Master mode	5	-	
$t_{h(SI)}$(1)		Slave mode	4	-	
$t_{a(SO)}$(1)(2)	Data output access time	Slave mode, f_{PCLK} = 24 MHz	0	$3t_{PCLK}$	
$t_{dis(SO)}$(1)(3)	Data output disable time	Slave mode	2	10	
$t_{v(SO)}$ (1)	Data output valid time	Slave mode (after enable edge)	-	25	
$t_{v(MO)}$(1)	Data output valid time	Master mode (after enable edge)	-	5	
$t_{h(SO)}$(1)	Data output hold time	Slave mode (after enable edge)	15	-	
$t_{h(MO)}$(1)		Master mode (after enable edge)	2	-	

1. Guaranteed by characterization results.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Figure 29. SPI timing diagram - slave mode and CPHA = 0

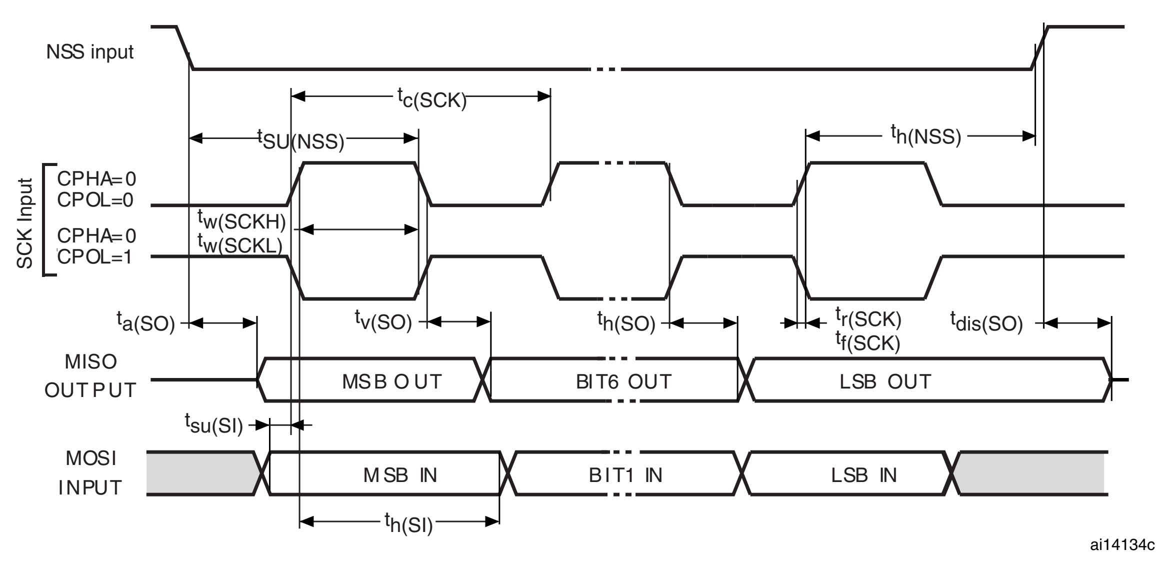
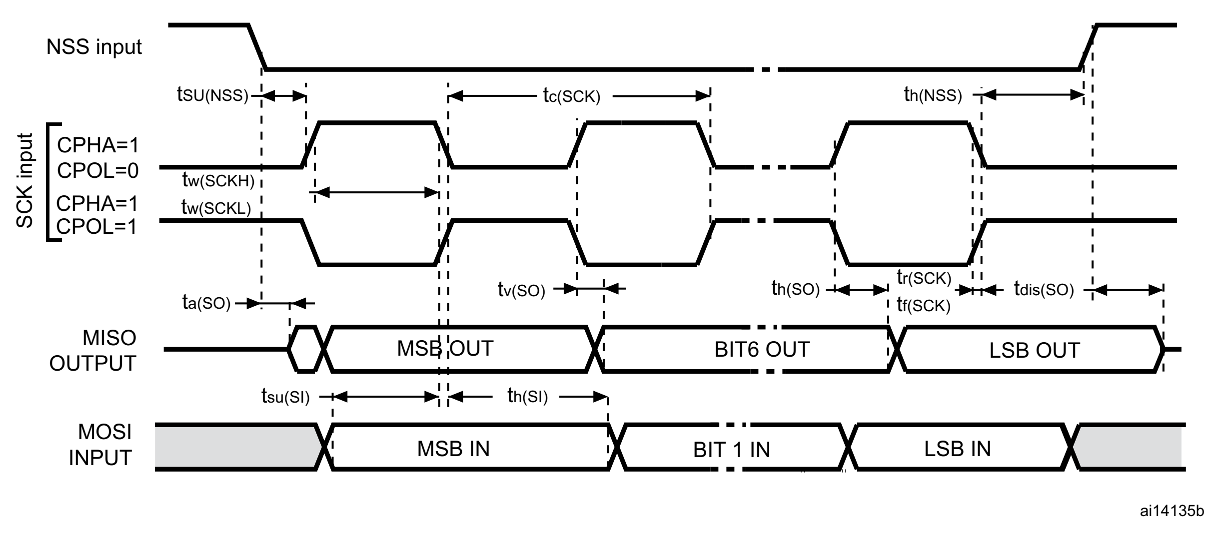
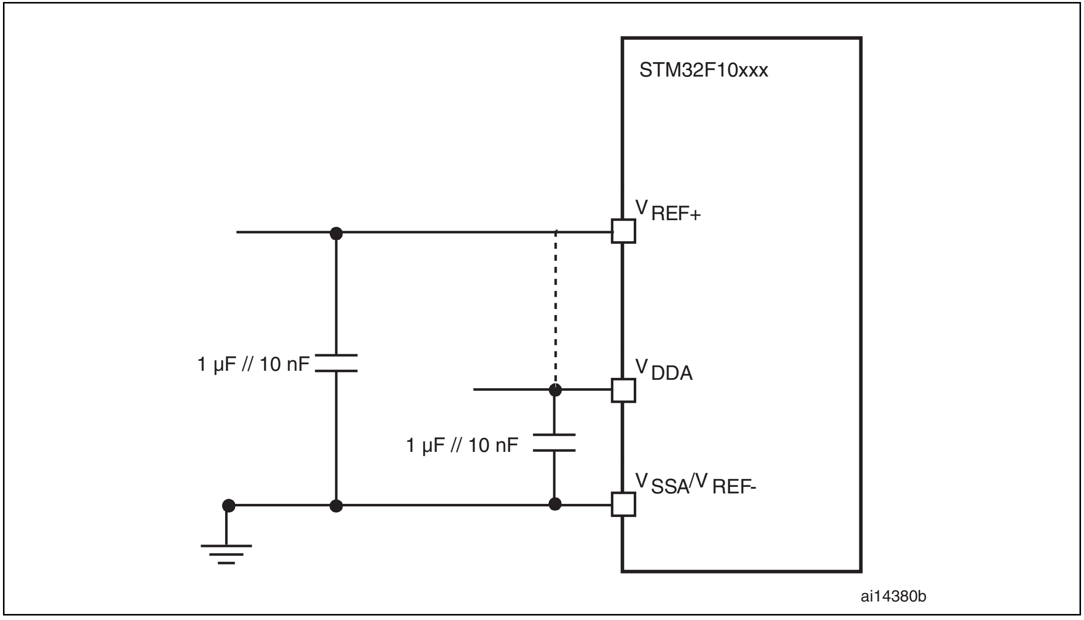


Figure 30. SPI timing diagram - slave mode and CPHA = 1[1]



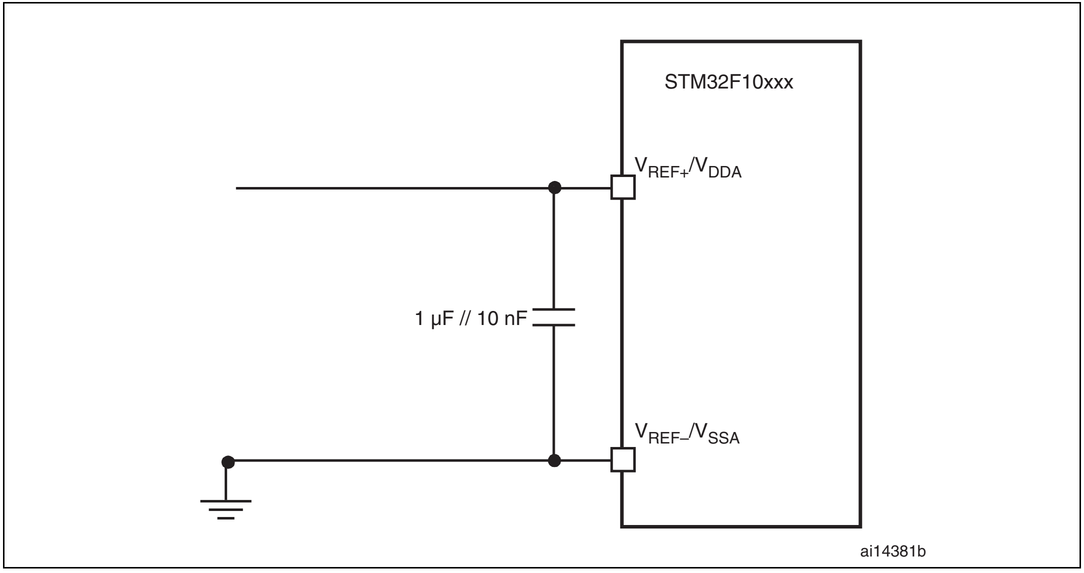
1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Figure 34. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} is available on 100-pin packages and on TFBGA64 packages. V_{REF-} is available on 100-pin packages only.

Figure 35. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

5.3.18 DAC electrical specifications

Table 46. DAC characteristics

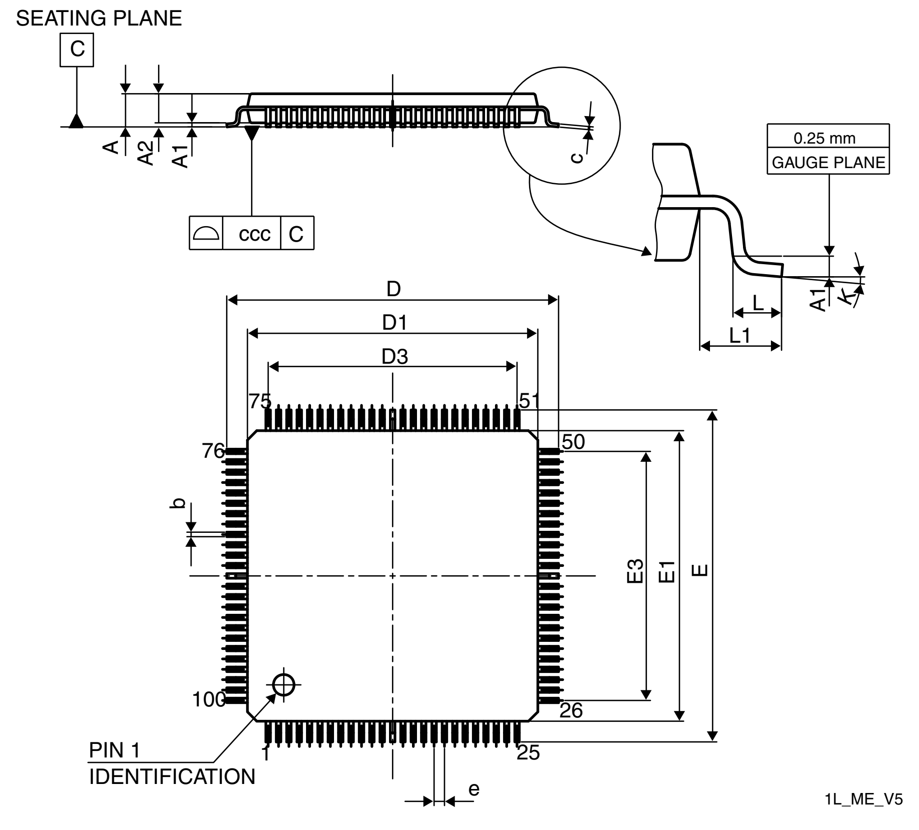
Symbol	Parameter	Min	Typ	Max(1)	Unit	Comments
V_{DDA}	Analog supply voltage	2.4	-	3.6	V	-
V_{REF+}	Reference supply voltage	2.4	-	3.6	V	V_{REF+} must always be below V_{DDA}
V_{SSA}	Ground	0	-	0	V	-
R_{LOAD}(2)	Resistive load with buffer ON	5	-	-	kΩ	-
R_O(1)	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
C_{LOAD}(1)	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min(1)	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{REF+} = 3.6 V and (0x155) and (0xEAB) at V_{REF+} = 2.4 V
DAC_OUT max(1)	Higher DAC_OUT voltage with buffer ON	-	-	$V_{DDA} - 0.2$	V	
DAC_OUT min(1)	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output excursion of the DAC.
DAC_OUT max(1)	Higher DAC_OUT voltage with buffer OFF	-	-	V_{REF+} – 1LSB	V	
$I_{DDVREF+}$	DAC DC current consumption in quiescent mode (Standby mode)	-	-	220	µA	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
I_{DDA}	DAC DC current consumption in quiescent mode (Standby mode)	-	-	380	µA	With no load, middle code (0x800) on the inputs
		-	-	480	µA	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
DNL(1)	Differential non linearity Difference between two consecutive code-1LSB)	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration
		-	-	±2	LSB	Given for the DAC in 12-bit configuration
INL(1)	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±1	LSB	Given for the DAC in 10-bit configuration
		-	-	±4	LSB	Given for the DAC in 12-bit configuration

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

6.1 LQFP100 package information

Figure 37. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline



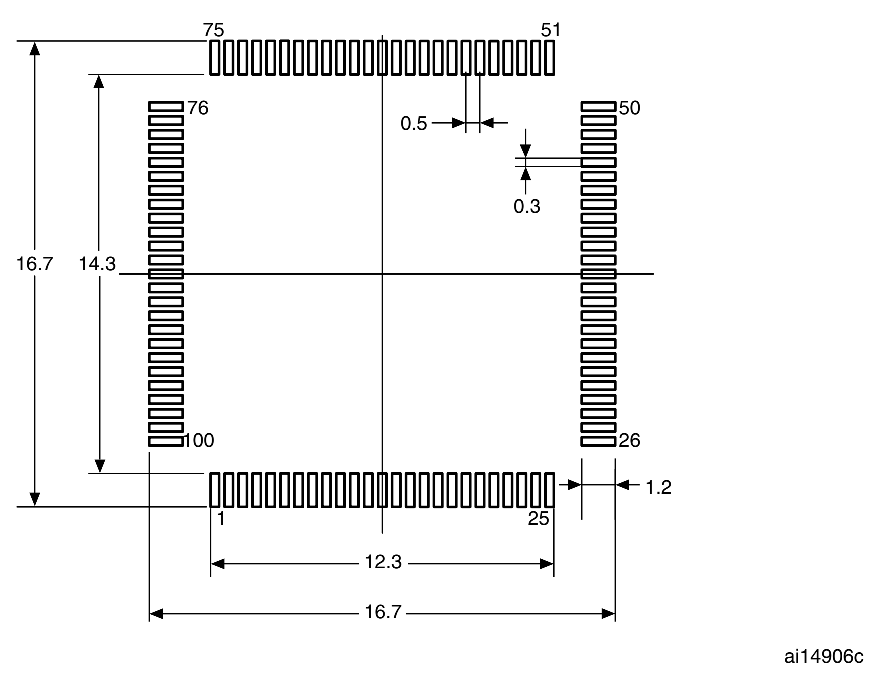
1. Drawing is not to scale. Dimensions are in millimeters.

Table 48. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

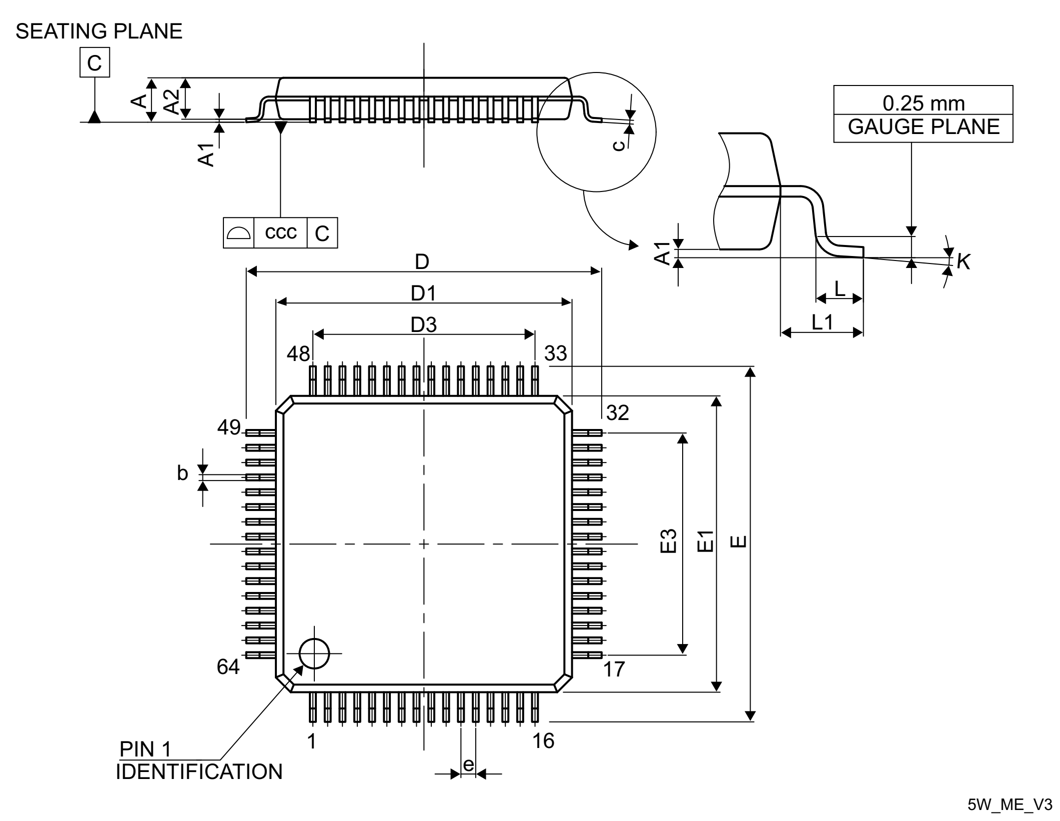
Figure 38. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint



1. Dimensions are in millimeters.

6.2 LQFP64 package information

Figure 40.LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package outline



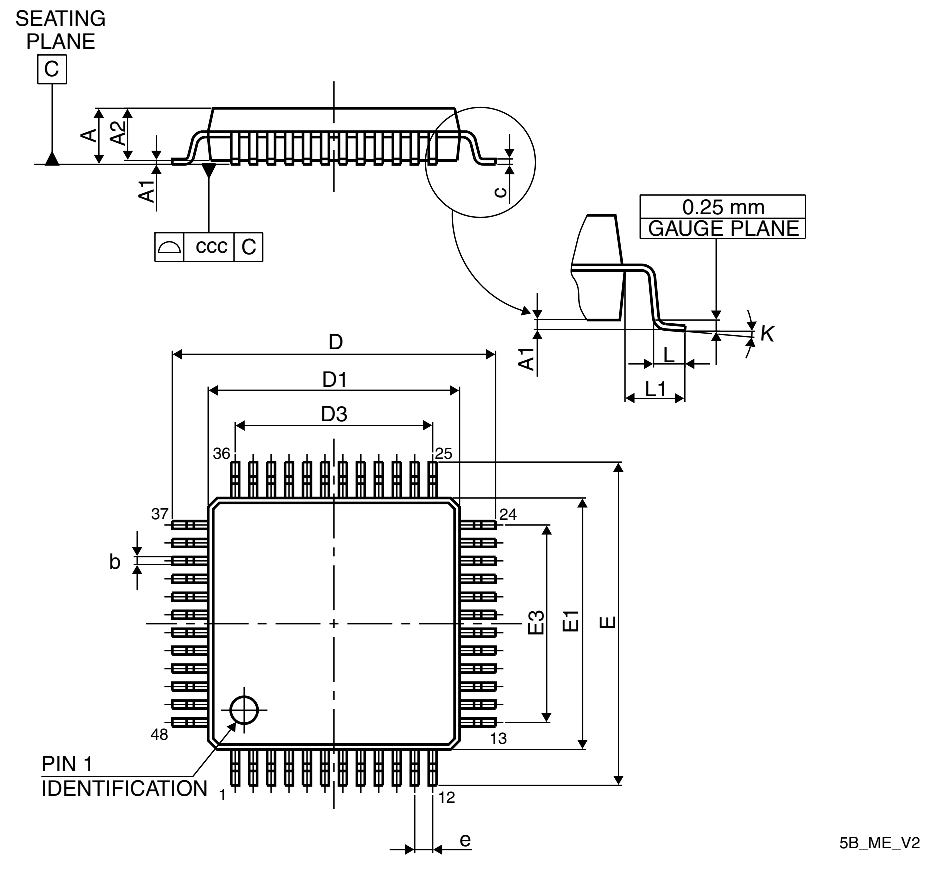
1. Drawing is not in scale.

Table 49. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.500	-	-	0.2953	-

6.4 LQFP48 package information

Figure 46. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 52. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622

6.5.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Table 54: Ordering information scheme*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F10xxx at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example: high-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output mode at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

$P_{INTmax\,=}$ 50 mA × 3.5 V= 175 mW

$P_{IOmax\,=\,20}$ × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW

$P_{Dmax\,=}$ 175 $_+$ 272 = 447 mW

Thus: P_{Dmax} = 447 mW

Using the values obtained in *Table 53* T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

T_{Jmax} = 82 °C + (45 °C/W × 447 mW) = 82 °C + 20.1 °C = 102.1 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C).

In this case, parts must be ordered at least with the temperature range suffix 6 (see *Table 54: Ordering information scheme*).

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 115 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

$P_{INTmax\,=}$ 20 mA × 3.5 V= 70 mW

$P_{IOmax\,=\,20}$ × 8 mA × 0.4 V = 64 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 64 mW:

$P_{Dmax\,=}$ 70 $_+$ 64 = 134 mW

Thus: P_{Dmax} = 134 mW